Vishay Semiconductors

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Hyperfast Rectifier, 60 A FRED Pt[®] G5



PRIMARY CHARACTERISTICS								
I _{F(AV)} 60 A								
V _R	1200 V							
V _F at I _F at 125 °C	1.7 V							
t _{rr}	38 ns							
T _J max.	175 °C							
Package	TO-247AD 2L							
Circuit configuration	Single							

FEATURES

- Hyperfast and optimized Q_{rr}
- · Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- FREE • 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V					
Average rectified forward current	I _{F(AV)}	T _C = 115 °C, D = 0.50	60						
Non-repetitive peak surge current	I _{FSM}	$T_{C} = 45 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ sine wave}$	460	А					
Repetitive peak forward current	I _{FRM}	T _C = 115 °C, D = 0.50, f = 20 kHz	120						
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS				MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-				
Forward valtage	V _F	I _F = 60 A	-	1.9	2.3	V			
Forward voltage		I _F = 60 A, T _J = 125 °C	-	1.7	-				
Deverse leakerse eurrent	I _R	V _R = V _R rated	-	-	50				
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V _R = 200 V	-	32	-	pF			
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH			





RoHS COMPLIANT

HALOGEN



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		I _F = 1.0 A, dI _F /dt =	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		38	-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	130	-	ns		
		T _J = 125 °C		-	200	-			
Deals receivers ourrent		T _J = 25 °C	I _F = 40 A dI _F /dt = 600 A/µs V _R = 400 V	-	22	-	А		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	39	-			
	0	T _J = 25 °C		-	1610	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	4080	-			
Powerse recovery time	+	T _J = 25 °C		-	100	-	20		
Reverse recovery time	t _{rr}	T _J = 125 °C		-	153	-	ns		
Deels receiver a surrent	I _{RRM}	T _J = 25 °C	I _F = 60 A dI _F /dt = 1000 A/µs	-	40	-	А		
Peak recovery current		T _J = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	67	-	A		
	<u> </u>	T _J = 25 °C		-	2590	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	6150	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UN										
Thermal resistance, junction-to-case	R _{thJC}		-	-	0.4	°C/W				
Weight			-	5.5	-	g				
Weight			-	0.2	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style TO-247AD 2L	E5PH6012L							

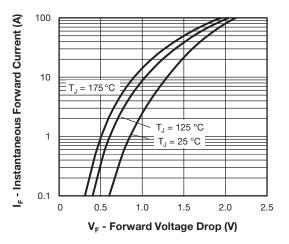


Fig. 1 - Typical Forward Voltage Drop Characteristics

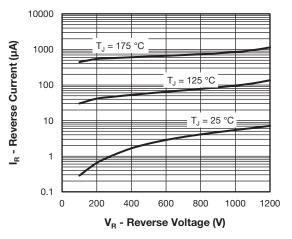


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

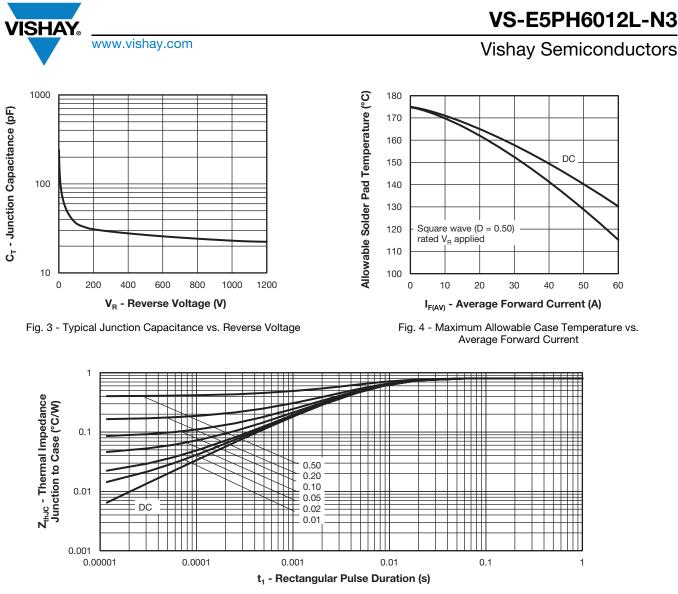


Fig. 5 - Thermal Impedance ZthJC Characteristics

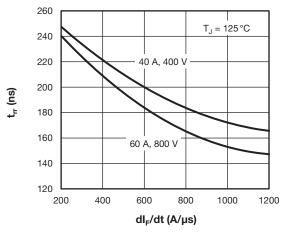


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

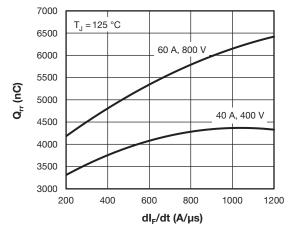


Fig. 7 - Typical Stored Charge vs. dl_F/dt

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VS-E5PH6012L-N3

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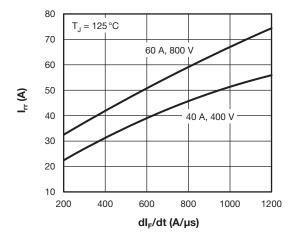


Fig. 8 - Typical Recovery Current vs. dl_F/dt

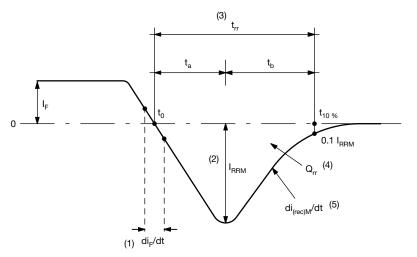


Fig. 9 - Reverse Recovery Waveform and Definitions

Notes

- (1) di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F , to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-E5PH6012L-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?95536							
Part marking information	www.vishay.com/doc?95648						

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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIN	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES		STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053				•		•		•

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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